

MOS FIELD EFFECT TRANSISTOR

NP90N06VLG

SWITCHING

N-CHANNEL POWER MOS FET

DESCRIPTION

The NP90N06VLG is N-channel MOS Field Effect Transistor designed for high current switching applications.

ORDERING INFORMATION

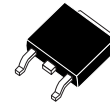
PART NUMBER	LEAD PLATING	PACKING	PACKAGE
NP90N06VLG-E1-AY ^{Note}	Pure Sn (Tin)	Tape 2500 p/reel	TO-252 (MP-3ZP) typ. 0.27 g
NP90N06VLG-E2-AY ^{Note}			

Note Pb-free (This product does not contain Pb in external electrode.)

FEATURES

- Logic level
- Built-in gate protection diode
- Super low on-state resistance
 $R_{DS(on)1} = 7.8 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 45 \text{ A)}$
 $R_{DS(on)2} = 12.5 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.5 \text{ V, } I_D = 35 \text{ A)}$
- High current rating
 $I_{D(DC)} = \pm 90 \text{ A}$
- Low input capacitance
 $C_{iss} = 4600 \text{ pF TYP.}$
- Designed for automotive application and AEC-Q101 qualified

(TO-252)



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	60	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±20	V
Drain Current (DC) (T _C = 25°C)	I _{D(DC)}	±90	A
Drain Current (pulse) ^{Note1}	I _{D(pulse)}	±180	A
Total Power Dissipation (T _C = 25°C)	P _{T1}	105	W
Total Power Dissipation (T _A = 25°C)	P _{T2}	1.2	W
Channel Temperature	T _{ch}	175	°C
Storage Temperature	T _{stg}	-55 to +175	°C
Repetitive Avalanche Current ^{Note2}	I _{AR}	32	A
Repetitive Avalanche Energy ^{Note2}	E _{AR}	102	mJ

Notes 1. $PW \leq 10 \mu s$, Duty Cycle $\leq 1\%$

2. $T_{ch} \leq 150^\circ\text{C}$, $R_G = 25 \Omega$

THERMAL RESISTANCE

Channel to Case Thermal Resistance	R _{th(ch-C)}	1.43	°C/W
Channel to Ambient Thermal Resistance	R _{th(ch-A)}	125	°C/W

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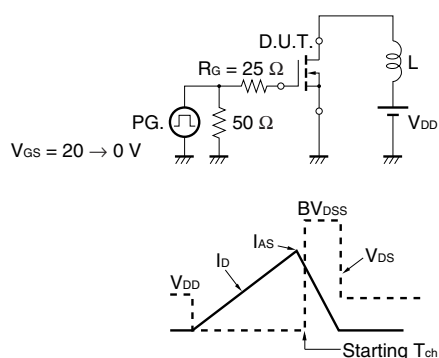
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ELECTRICAL CHARACTERISTICS (T_A = 25°C)

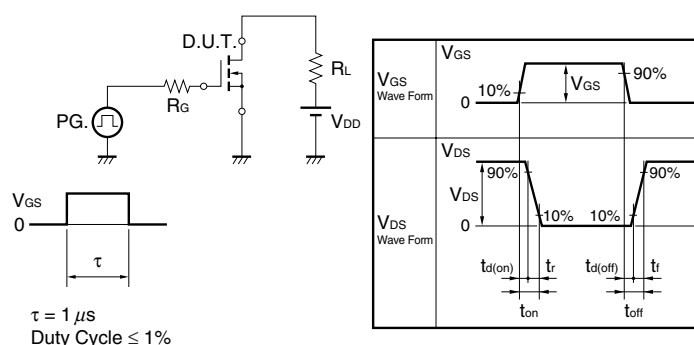
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			1	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μA
Gate to Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.4		2.5	V
Forward Transfer Admittance ^{Note}	y _{fs}	V _{DS} = 5 V, I _D = 45 A	30	66		S
Drain to Source On-state Resistance ^{Note}	R _{DS(on)1}	V _{GS} = 10 V, I _D = 45 A		6.2	7.8	mΩ
	R _{DS(on)2}	V _{GS} = 4.5 V, I _D = 35 A		7.5	12.5	mΩ
Input Capacitance	C _{iss}	V _{DS} = 25 V,		4600	6900	pF
Output Capacitance	C _{oss}	V _{GS} = 0 V,		370	560	pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		220	400	pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 30 V, I _D = 45 A,		17	34	ns
Rise Time	t _r	V _{GS} = 10 V,		13	33	ns
Turn-off Delay Time	t _{d(off)}	R _G = 0 Ω		76	152	ns
Fall Time	t _f			7	18	ns
Total Gate Charge	Q _G	V _{DD} = 48 V,		90	135	nC
Gate to Source Charge	Q _{GS}	V _{GS} = 10 V,		13		nC
Gate to Drain Charge	Q _{GD}	I _D = 90 A		26		nC
Body Diode Forward Voltage ^{Note}	V _{F(S-D)}	I _F = 90 A, V _{GS} = 0 V		0.9	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 90 A, V _{GS} = 0 V,		38		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100 A/μs		56		nC

Note Pulsed test

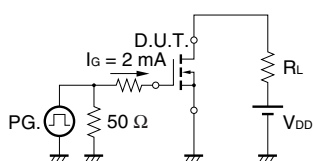
TEST CIRCUIT 1 AVALANCHE CAPABILITY



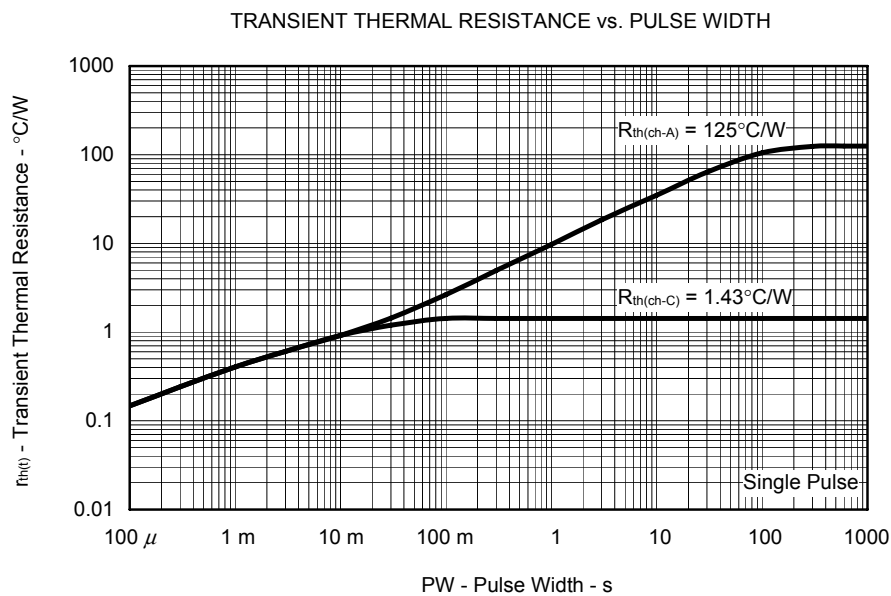
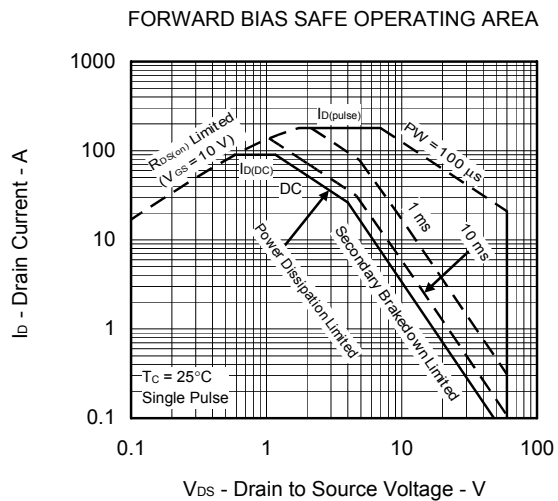
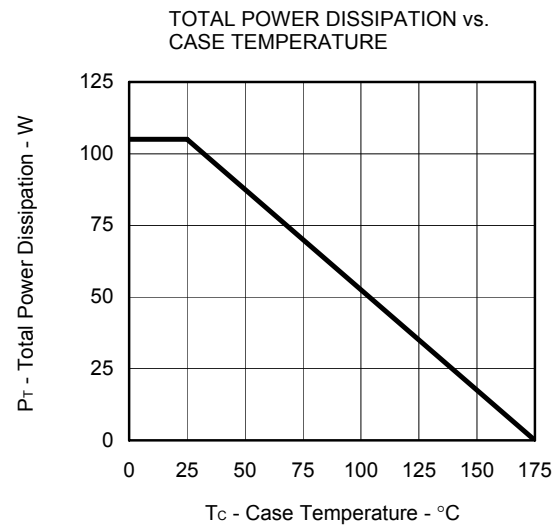
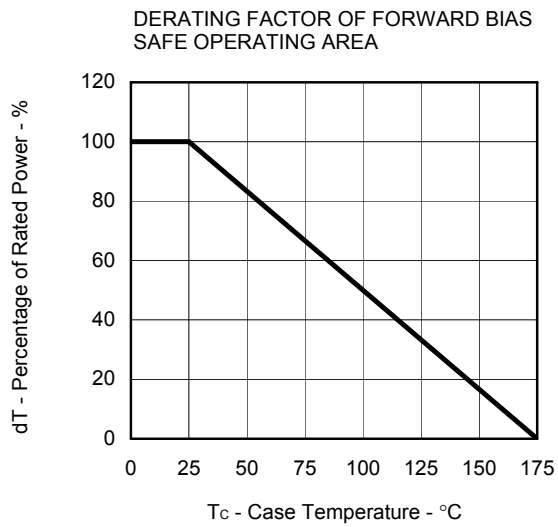
TEST CIRCUIT 2 SWITCHING TIME



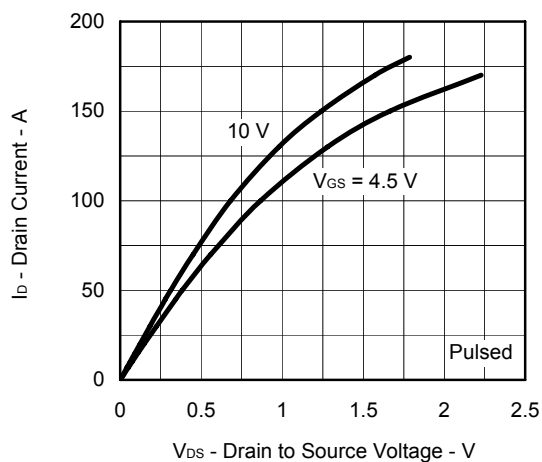
TEST CIRCUIT 3 GATE CHARGE



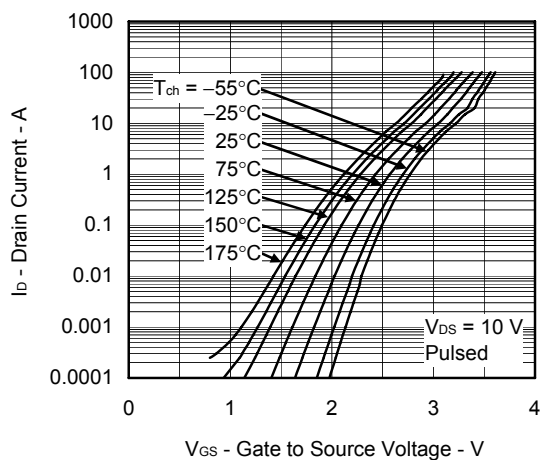
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)



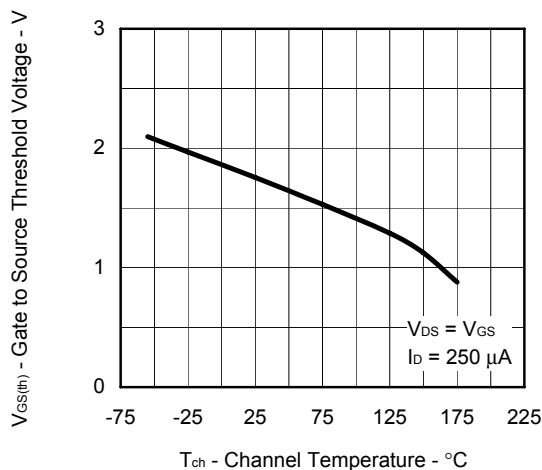
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



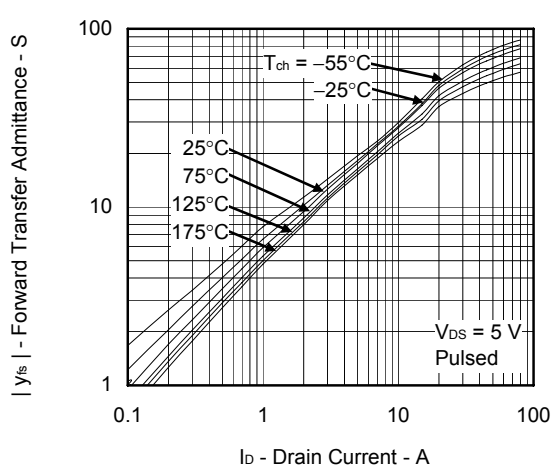
FORWARD TRANSFER CHARACTERISTICS



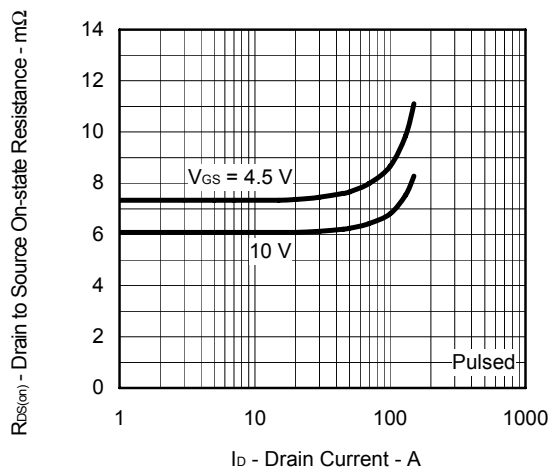
GATE TO SOURCE THRESHOLD VOLTAGE vs.
CHANNEL TEMPERATURE



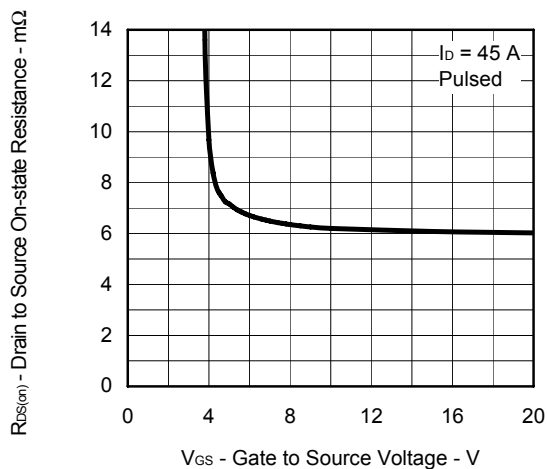
FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT



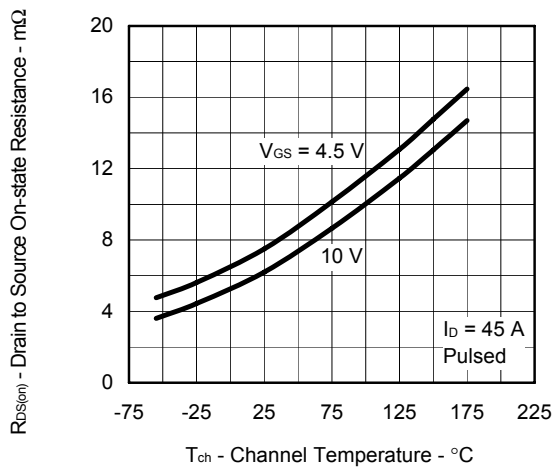
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENT



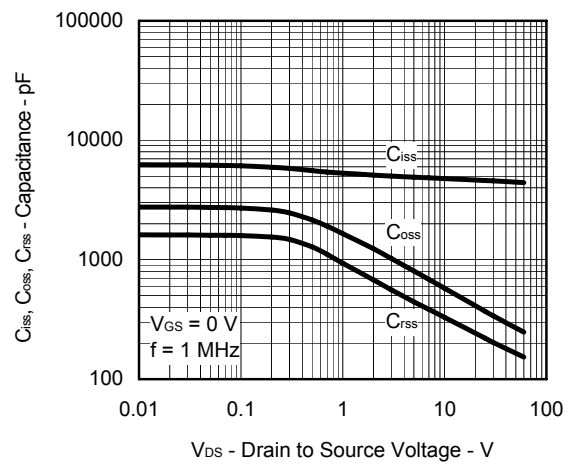
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE



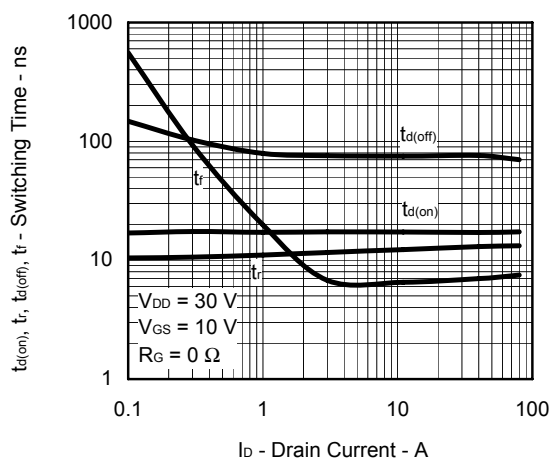
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



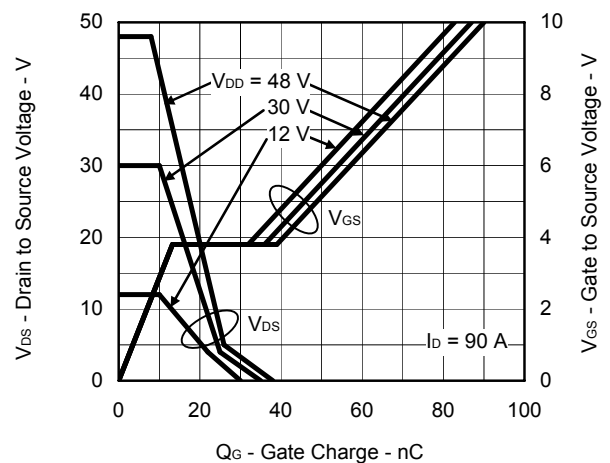
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



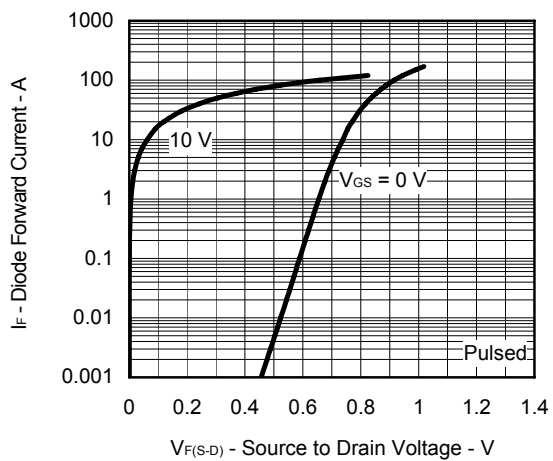
SWITCHING CHARACTERISTICS



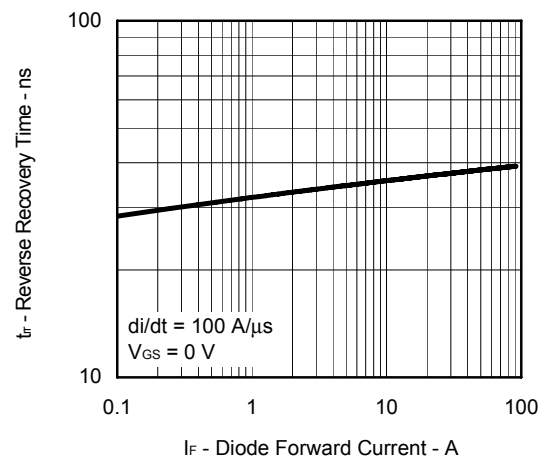
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

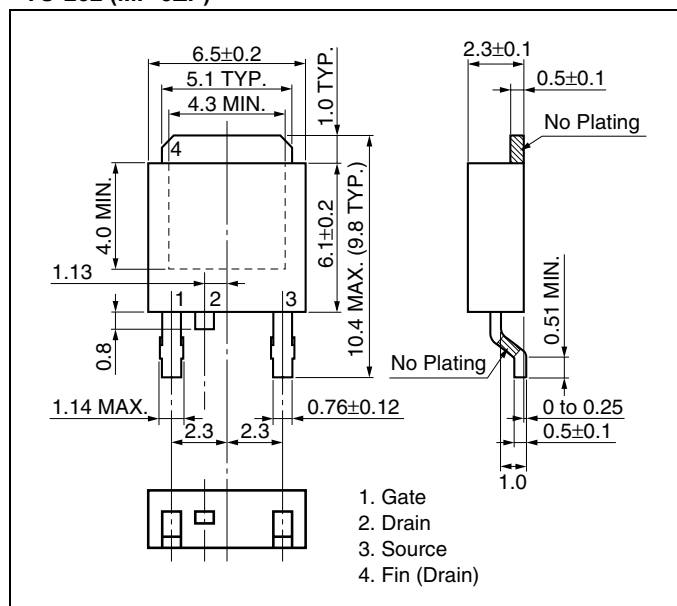


REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT

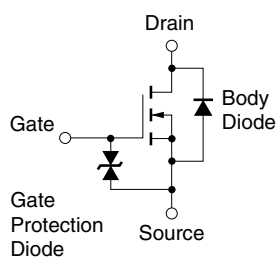


PACKAGE DRAWING (Unit: mm)

TO-252 (MP-3ZP)



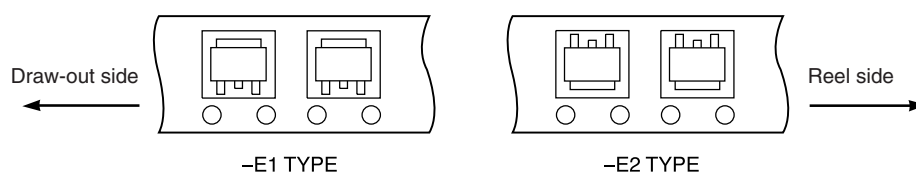
EQUIVALENT CIRCUIT



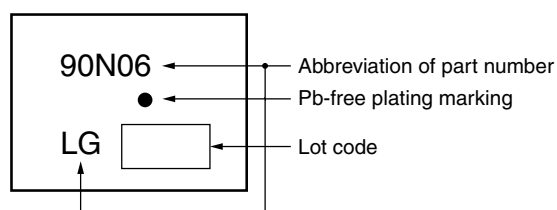
Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

TAPE INFORMATION

There are two types (-E1, -E2) of taping depending on the direction of the device.



MARKING INFORMATION



RECOMMENDED SOLDERING CONDITIONS

The NP90N06VLG should be soldered and mounted under the following recommended conditions.

For soldering methods and conditions other than those recommended below, please contact an NEC Electronics sales representative.

For technical information, see the following website.

Semiconductor Device Mount Manual (<http://www.necel.com/pkg/en/mount/index.html>)

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Maximum temperature (Package's surface temperature): 260°C or below Time at maximum temperature: 10 seconds or less Time of temperature higher than 220°C: 60 seconds or less Preheating time at 160 to 180°C: 60 to 120 seconds Maximum number of reflow processes: 3 times Maximum chlorine content of rosin flux (percentage mass): 0.2% or less	IR60-00-3
Partial heating	Maximum temperature (Pin temperature): 350°C or below Time (per side of the device): 3 seconds or less Maximum chlorine content of rosin flux: 0.2% (wt.) or less	P350

Caution Do not use different soldering methods together (except for partial heating).

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